## **Thyristor \ Diode Module**

= 2x 1800 V

110 A

 $V_{\mathsf{T}}$ 1.21 V

### Phase leg

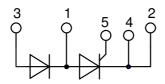
#### Part number

#### **MCMA110PD1800TB**



Backside: isolated

**F1** E72873



#### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

#### **Applications:**

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter AC power control
- Lighting and temperature control

#### Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- · Reduced weight
- Advanced power cycling

#### Terms \_Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

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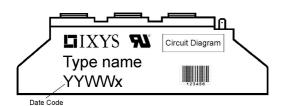


Rectifier					Ratings		1
Symbol	Definition	Conditions		min.	typ.	max.	Uni
V <sub>RSM/DSM</sub>	max. non-repetitive reverse/forwa	rd blocking voltage	$T_{VJ} = 25^{\circ}C$			1900	٧
V <sub>RRM/DRM</sub>	max. repetitive reverse/forward blo	ocking voltage	$T_{VJ} = 25^{\circ}C$			1800	٧
I <sub>R/D</sub>	reverse current, drain current	$V_{R/D} = 1800 \text{ V}$	$T_{VJ} = 25^{\circ}C$			100	μΑ
		$V_{R/D} = 1800 \text{ V}$	$T_{VJ} = 140$ °C			10	mΑ
V <sub>T</sub>	forward voltage drop	$I_T = 110 A$	$T_{VJ} = 25^{\circ}C$			1.24	٧
		$I_T = 220 A$				1.52	٧
		$I_T = 110 A$	T <sub>VJ</sub> = 125°C			1.21	٧
		$I_{T} = 220 \text{ A}$				1.57	٧
I <sub>TAV</sub>	average forward current	$T_{C} = 85^{\circ}C$	T <sub>vJ</sub> = 140°C			110	Д
T(RMS)	RMS forward current	180° sine				170	Α
V <sub>T0</sub>	threshold voltage	and a detient and a	$T_{VJ} = 140$ °C			0.85	٧
r <sub>T</sub>	slope resistance } for power in	oss calculation only				3.3	mΩ
R <sub>thJC</sub>	thermal resistance junction to case	e				0.3	K/W
R <sub>thCH</sub>	thermal resistance case to heatsing	nk			0.20		K/W
P <sub>tot</sub>	total power dissipation		T <sub>C</sub> = 25°C			380	W
I <sub>TSM</sub>	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			1.90	kΑ
		t = 8.3  ms; (60 Hz), sine	$V_R = 0 V$			2.05	kΑ
		t = 10 ms; (50 Hz), sine	T <sub>VJ</sub> = 140°C			1.62	kA
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			1.75	kΑ
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			18.1	kA <sup>2</sup> s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			17.5	kA2s
		t = 10 ms; (50 Hz), sine	T <sub>VJ</sub> = 140°C			13.0	kA2s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			12.7	į
C <sub>J</sub>	junction capacitance	$V_R = 400 \text{V}$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		95		рF
P <sub>GM</sub>	max. gate power dissipation	t <sub>P</sub> = 30 μs	T <sub>C</sub> = 140°C			10	·
- GIWI	mani gate perrer alcorpation	$t_P = 300 \mu s$	0			5	W
$P_{GAV}$	average gate power dissipation					0.5	W
(di/dt) <sub>cr</sub>	critical rate of rise of current	T <sub>v.i</sub> = 140°C; f = 50 Hz r	epetitive, $I_T = 330 \text{ A}$			150	A/μs
( / cr	$t_{\rm p} = 200  \mu \rm s; di_{\rm g}/dt = 0.45  A/\mu \rm s;$						7.4 [4.6]
			non-repet., $I_{T} = 110 \text{ A}$			500	A/μs
(dv/dt) <sub>cr</sub>	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{V,I} = 140^{\circ}C$			1000	V/µs
(a v/at/cr	omical rate of not of rollage	R <sub>GK</sub> = ∞; method 1 (linear volta				.000	17μο
<b>V</b> <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 6 V	$T_{VJ} = 25^{\circ}C$			1.5	٧
♥ G1	gare angger rentage	· b = 3 ·	$T_{VJ} = -40^{\circ}C$			1.6	٧
I <sub>GT</sub>	gate trigger current	$V_D = 6 \text{ V}$	$T_{VJ} = 40^{\circ} \text{C}$ $T_{VJ} = 25^{\circ} \text{C}$			150	mA
•GT	gate ingger our en	<b>V</b> D = 0 <b>V</b>	$T_{VJ} = -40$ °C			200	mA
V <sub>GD</sub>	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DBM}$	$T_{VJ} = 140^{\circ}C$			0.2	V
	gate non-trigger current	V <sub>D</sub> — 73 V <sub>DRM</sub>	17/ = 140 0			10	1
l <sub>gD</sub>		10.00	T 05°C				mA
l <sub>L</sub>	latching current	$t_p = 10 \mu s$ $I_G = 0.45 A$ ; $di_G/dt = 0.45 A/\mu$	$T_{VJ} = 25$ °C			200	mA
ı	holding current	$V_{D} = 6 \text{ V } R_{GK} = \infty$	$T_{VJ} = 25$ °C			200	mA
I <sub>H</sub>	gate controlled delay time	$V_D = 0$ $V_{GK} = \infty$ $V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25 ^{\circ}\text{C}$ $T_{VJ} = 25 ^{\circ}\text{C}$			200	<u> </u>
t <sub>gd</sub>	gate controlled delay little					2	μs
	$I_{G} = 0.45 \text{ A}; \text{ di}_{G}/\text{dt} = 0.45 \text{ A}/\mu\text{s}$ $turn\text{-}off time \qquad V_{R} = 100 \text{ V}; \ I_{T} = 110 \text{ A}; \ V = \frac{2}{3} \text{ V}_{DRM}  T_{VJ} = 125 \text{ °C}$				105		1
t <sub>q</sub>		ν = 100 V· I = 110 Δ· V = 4	72 V I −125 °(;		185		μs



# **MCMA110PD1800TB**

Package	Package TO-240AA			Ratings				
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current	per terminal					200	Α
T <sub>VJ</sub>	virtual junction temperature				-40		140	°C
Top	operation temperature				-40		125	°C
T <sub>stg</sub>	storage temperature				-40		125	°C
Weight						81		g
M <sub>D</sub>	mounting torque				2.5		4	Nm
$\mathbf{M}_{_{\mathbf{T}}}$	terminal torque				2.5		4	Nm
d <sub>Spp/App</sub>	araanaga diatanaa an aurfa	oo Latriking diatanoo through air	terminal to terminal	13.0	9.7			mm
d <sub>Spb/Apb</sub>	creepage distance on surface   striking distance through		terminal to backside	16.0	16.0			mm
V <sub>ISOL</sub>	isolation voltage	t = 1 second		•	4800			٧
1002		t = 1 minute	50/60 Hz, RMS; IISOL ≤ 1 mA		4000			٧



### Part description

M = Module

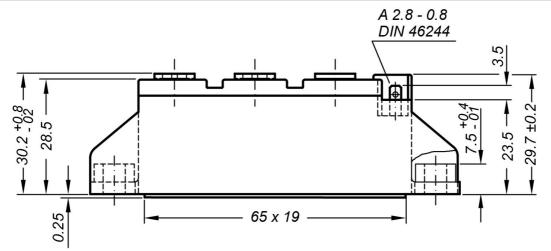
M = Module
C = Thyristor (SCR)
M = Thyristor
A = (up to 1800V)
110 = Current Rating [A]
PD = Phase leg 1800 = Reverse Voltage [V] TB = TO-240AA-1B

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA110PD1800TB	MCMA110PD1800TB	Box	36	

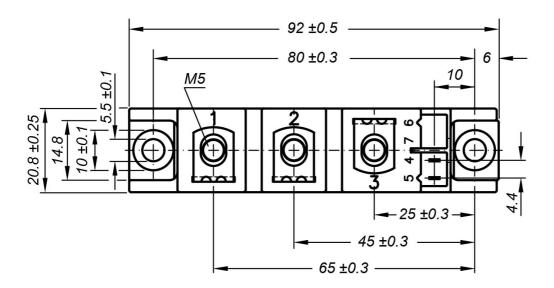
Equiva	alent Circuits for	Simulation	* on die level	$T_{VJ} = 140 ^{\circ}\text{C}$
$I \rightarrow V_0$	$R_0$	Thyristor		
V <sub>0 max</sub>	threshold voltage	0.85		V
$R_{0 \text{ max}}$	slope resistance *	2.1		$m\Omega$



#### **Outlines TO-240AA**

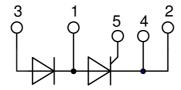


General tolerance: DIN ISO 2768 class "c"



Optional accessories: Keyed gate/cathode twin plugs Wire length: 350 mm, gate = white, cathode = red UL 758, style 3751

Type **ZY 200L** (L = Left for pin pair 4/5)





#### **Thyristor**

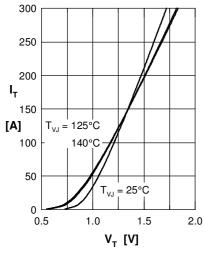


Fig. 1 Forward characteristics

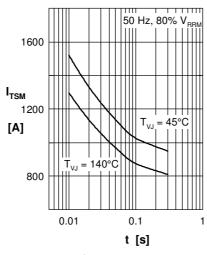


Fig. 2 Surge overload current  $I_{TSM}$ : crest value, t: duration

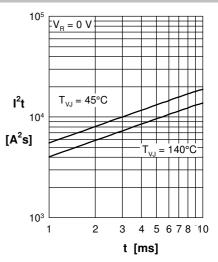


Fig. 3 I<sup>2</sup>t versus time (1-10 s)

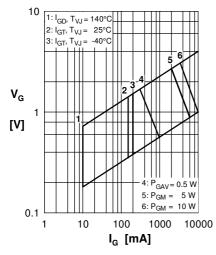


Fig. 4 Gate voltage & gate current

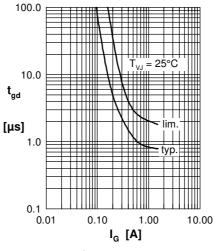


Fig. 5 Gate controlled delay time t<sub>ad</sub>

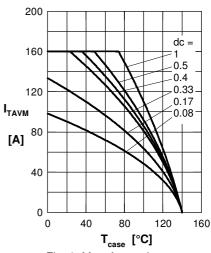


Fig. 6 Max. forward current at case temperature

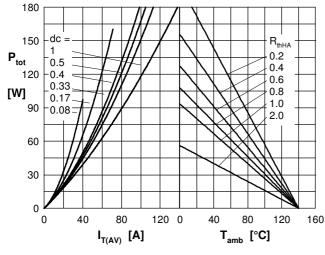


Fig. 7a Power dissipation versus direct output current Fig. 7b and ambient temperature

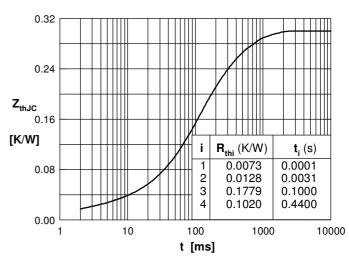


Fig. 8 Transient thermal impedance junction to case